

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CBO}	collector-base voltage	open emitter	-	50	V	
V_{CEO}	collector-emitter voltage	open base	-	50	V	
V_{EBO}	emitter-base voltage	open collector	-	5	V	
I_C	collector current		-	100	mA	
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA	
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	100	mA	
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1][2]	-	250	mW
			[3][2]	-	590	mW
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-55	+150	°C	
T_{stg}	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, mounting pad for collector 1 cm².

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	500	K/W
			[3][2]	-	-	212	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, mounting pad for collector 1 cm².

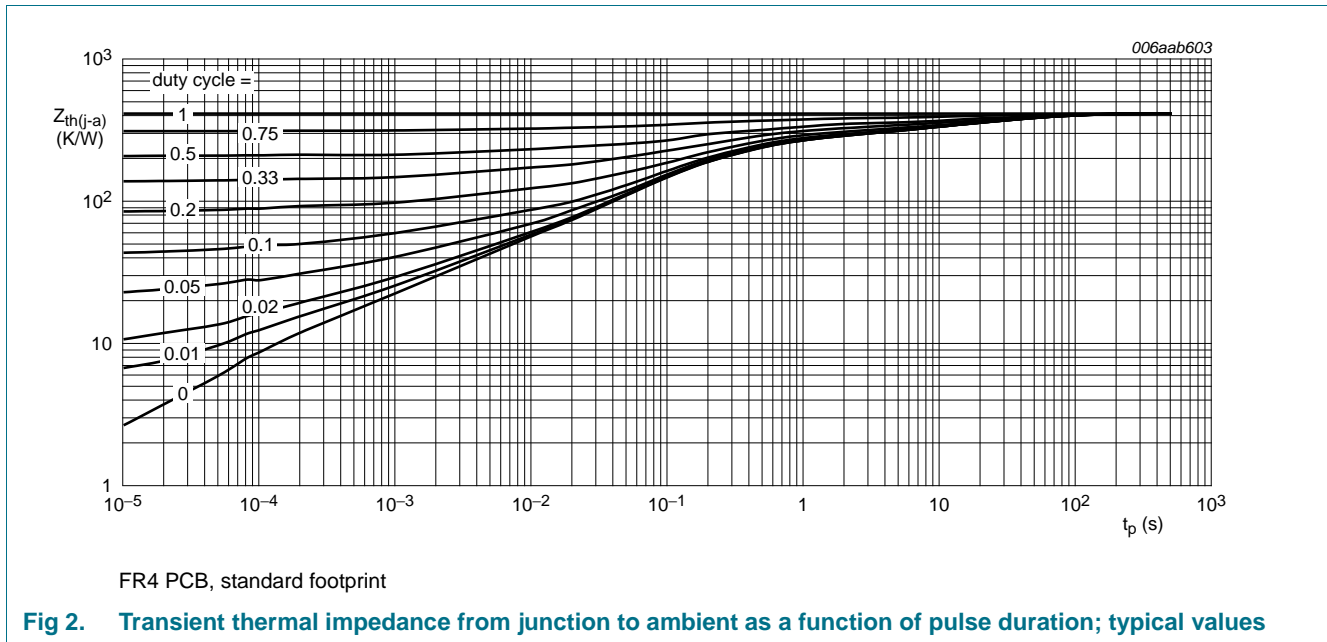


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 8. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit				
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	100	nA				
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	μA				
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0\text{ A}$	-	-	100	nA				
h_{FE}	DC current gain	$V_{CE} = 6\text{ V}; I_C = 1\text{ mA}$								
							2PC4617QMB	120	-	270
							2PC4617RMB	180	-	390
V_{CEsat}	collector-emitter saturation voltage	$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	[1]	-	200	mV				
f_T	transition frequency	$V_{CE} = 12\text{ V}; I_C = 2\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz				
C_c	collector capacitance	$V_{CB} = 12\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	1.5	pF				

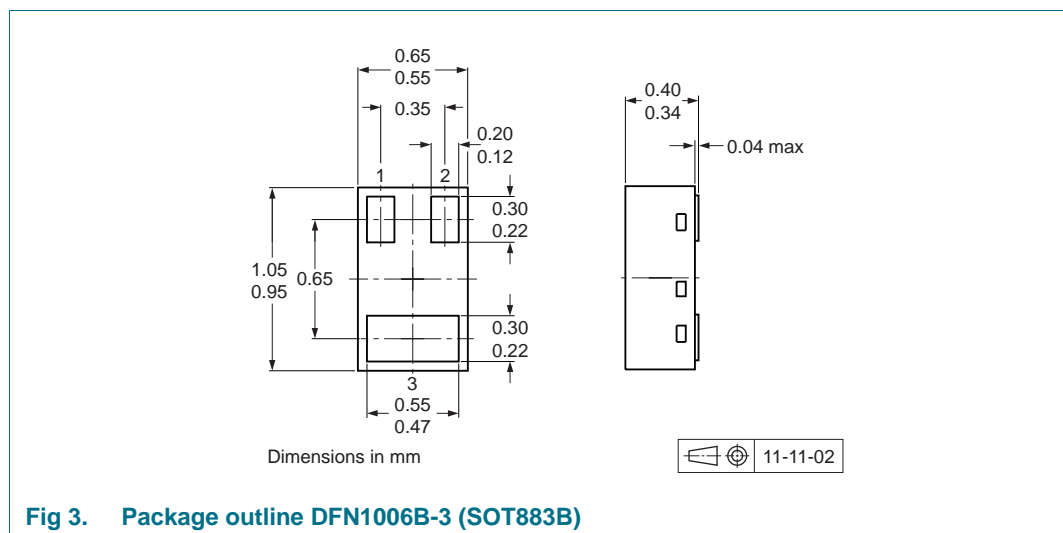
[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

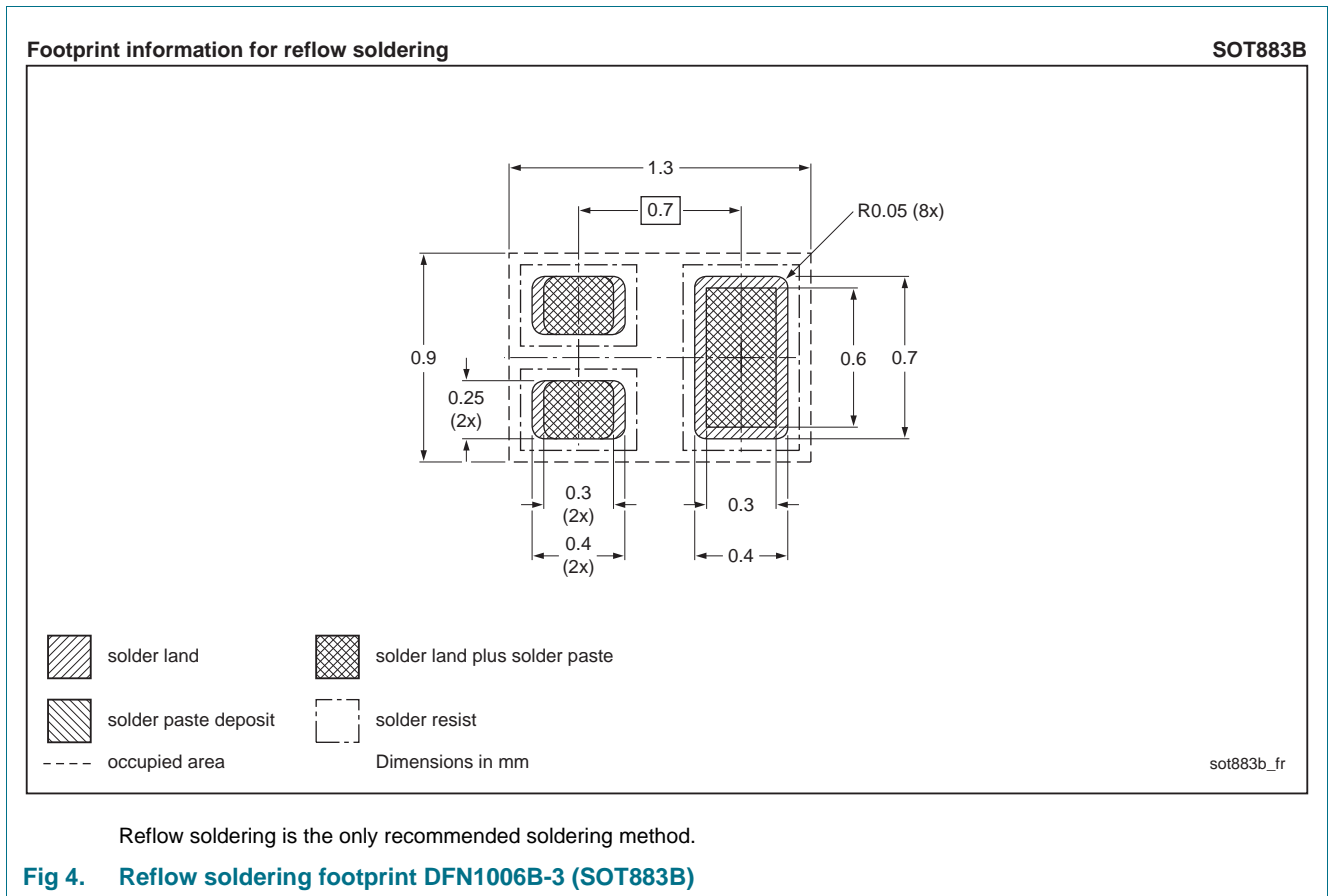
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity
			10000
2PC4617xMB series	DFN1006B-3 (SOT883B)	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering



12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2PC4617XMB_SER v.1	20120326	Product data sheet	-	-

